

**AMENDMENTS TO THE ABSTRACT**

Please substitute the following paragraph(s) for the abstract now appearing in the currently filed specification:

The present invention provides a ~~method for manufacturing~~ method for an SOI wafer with a high productivity in which generation of a void is suppressed in manufacturing the SOI wafer. ~~The method for~~ In a manufacturing method for an SOI wafer of the present invention ~~comprises the steps of: forming~~ in which two starting wafers are prepared, an insulating layer is formed on at least one ~~wafer of the~~ two starting wafers; and ~~adhering~~ the one wafer is adhered to the other wafer without using an adhesive, ~~wherein there is used as agent~~, the starting ~~wafer a~~ wafer having wafers each with no line defect on a surface thereof. ~~Also, the method for~~ are used. In a manufacturing method for an SOI wafer of the present invention ~~comprises the steps of: forming~~ in which two starting wafers are prepared, an insulating layer is formed on at least one ~~wafer of the~~ two starting wafers; and ~~adhering~~ the one wafer is adhered to the other wafer without using an adhesive, ~~wherein agent~~, the starting ~~wafer is~~ wafers are subjected to a high temperature heat treatment in advance.